REMARKS

The Applicant respectfully requests that the amendment described herein be entered into the record prior to examination and consideration of the above-identified application. The Examiner is invited to contact Applicant's Representatives at the below-listed telephone number if there are any questions regarding this amendment or if prosecution of this application may be assisted thereby.

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

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Date 9-22-03

By _____
Marvin L. Beekman
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 22nd day of September, 2003.

Amy Moriarty
Name

_____
Signature

2818

PATENT

SN 10/028001

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Leonard Forbes et al.	Examiner:	Tu-Tu V. Ho
Serial No.:	10/028001	Group Art Unit:	2818
Filed:	December 20, 2001	Docket:	1303.035US1
Title:	PROGRAMMABLE ARRAY LOGIC OR MEMORY WITH P-CHANNEL DEVICES AND ASYMMETRICAL TUNNEL BARRIERS		

COMMUNICATION CONCERNING CO-PENDING APPLICATION(S)

Noted, TH, 11/14/03

Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related co-pending application(s) in the above-identified patent application:

Serial No.	Filing Date	Attorney Docket	Title
09/945395	August 30, 2001	1303.019US1	DRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/943134	August 30, 2001	1303.020US1	PROGRAMMABLE ARRAY LOGIC OR MEMORY DEVICES WITH ASYMMETRICAL TUNNEL BARRIERS
09/945512	August 30, 2001	1303.027US1	IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS
09/945554	August 30, 2001	1303.028US1	SRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW TUNNEL BARRIER INTERPOLY INSULATORS
10/081818	February 20, 2002	1303.045US1	ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW ASYMMETRICAL TUNNEL BARRIER INTERPLOY INSULATORS

10/177096	June 21, 2002	1303.063US1	GRADED COMPOSITION METAL OXIDE TUNNEL BARRIER INTERPOLY INSULATORS

Respectfully submitted,

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Name Amy Moriarty Signature